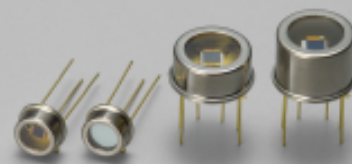


PbSe photoconductive detector P791/P2038/P2680 series, P3207-05

Detection capability up 5 μm range (TE-cooled type)



Hamamatsu provides various types of PbSe photoconductive cells including room temperature operation types and thermoelectrically cooled types. Cooled type PbSe photoconductive cells offer higher sensitivity and improved S/N, and are widely used in precision photometry such as in analytical instruments.

Features

- High-speed response
- Room temperature operation
Compared to other types of detectors used in the same wavelength range, PbSe cells have higher response speed and can also operate at room temperature, making them useful in a wide range of applications such as gas analyzers, etc.
- Lower temperature detection limit: 50 °C approx.

Applications

- Radiation thermometer
- Flame detector
- Gas analyzer
- Film thickness gauge

Accessories (Optional)

- Heatsink for one-stage TE-cooled type A3179
- Heatsink for two-stage TE-cooled type A3179-01
- Temperature controller for TE-cooled type C1103-04
- Preamplifier for PbS/PbSe photoconductive detector C3757-02
- Infrared detector module with preamp Non-cooled type P4245
Cooled type P4639

■ Specification / Absolute maximum ratings

Type No.	Dimensional outline	Package	Cooling	Active area (mm)	Thermistor resistance (k Ω)	Absolute maximum ratings				
						Thermistor power dissipation (mW)	TE-cooler current dissipation (A)	Supply voltage (V)	Operating temperature Topr (°C)	Storage temperature Tstg (°C)
P791-11	①	TO-5	Non-cooled	2 × 2	-	-	-	100	-30 to +50	-55 to +60
P791-13				3 × 3						
P3207-05	②			2 × 2						
P2038-02	③	TO-8	One-stage TE-cooled	2 × 2	9	0.2	1.5	100	-30 to +50	-55 to +60
P2038-03			Two-stage TE-cooled	3 × 3			1.0			
P2680-02	④			2 × 2						
P2680-03				3 × 3						

■ Electrical and optical characteristics (Typ. unless otherwise noted)

Type No.	Measurement condition	Peak sensitivity wavelength λ_p	Cut-off wavelength λ_c	Photo sensitivity S^*2 $\lambda=\lambda_p$ $V_s=15\text{ V}$		D^* (500, 600, 1)		D^* (λ_p , 600, 1)	Rise time t_r 0 to 63 %	Dark resistance R_d
	Element temperature T								Max. (μs)	
	($^{\circ}C$)	(μm)	(μm)	Min. (V/W)	Typ. (V/W)	Min. ($cm\text{ Hz}^{1/2}/W$)	Typ. ($cm\text{ Hz}^{1/2}/W$)	($cm\text{ Hz}^{1/2}/W$)	($M\Omega$)	
P791-11	25	4.0	4.8	7×10^2	1×10^3	5×10^7	1×10^8	1×10^9	3	0.3 to 1.5
P791-13				3×10^2	5×10^2					
P3207-05 *1		4.3	7×10^2	1×10^3						
P2038-02	-10	4.1	5.1	2.2×10^3	3×10^3	1×10^8	3×10^8	3×10^9	5	1.7 to 7.0
P2038-03				1×10^3	1×10^3					
P2680-02	-20	4.2	5.2	2.7×10^3	4×10^3	2×10^8	4×10^8	4×10^9		
P2680-03				1.2×10^3	2×10^3					

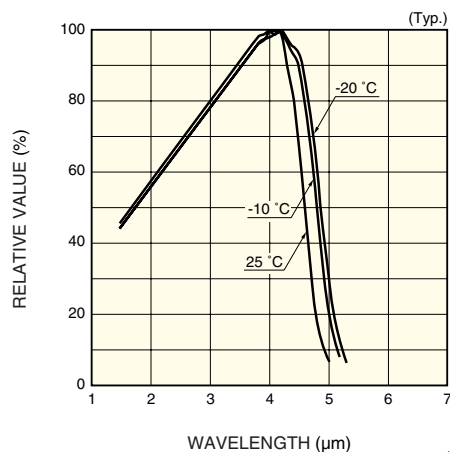
*1: Half width 400 nm

*2: Chopping frequency: 600 Hz, load resistance: nearly equal to detector element dark resistance

SOLID STATE DIVISION

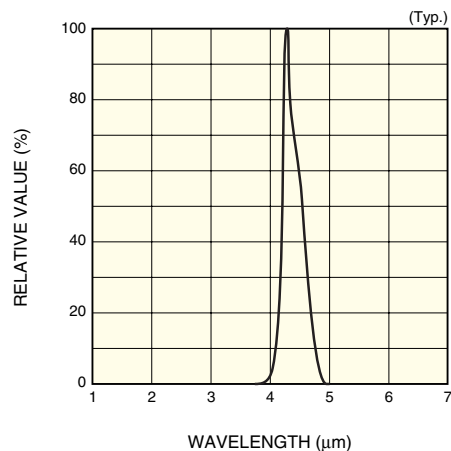
Spectral response

P791/P2038/P2680 series



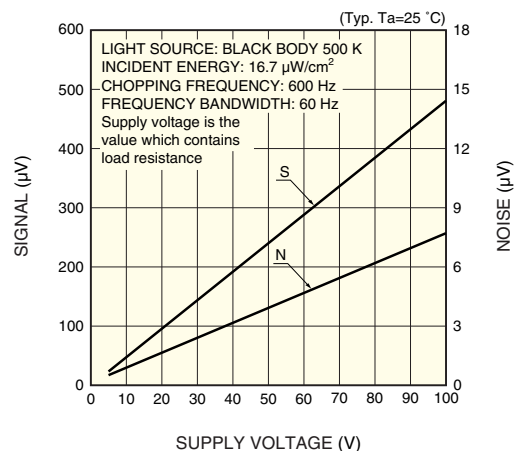
KIRDB0280EA

P3207-05



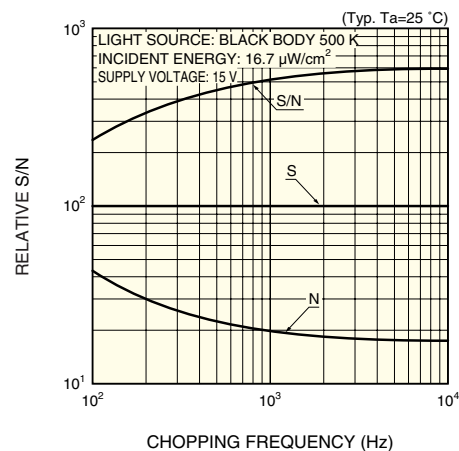
KIRDB0281EA

S/N vs. supply voltage



KIRDB0052EC

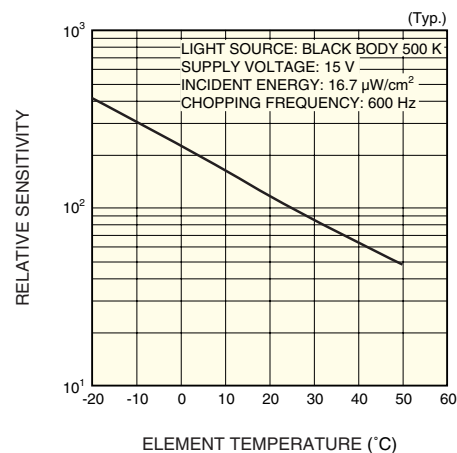
S/N vs. chopping frequency



KIRDB0053EB

Increasing the chopping frequency reduces the 1/f noise and results in an S/N improvement. The S/N can also be improved by narrowing the noise bandwidth using a lock-in amplifier.

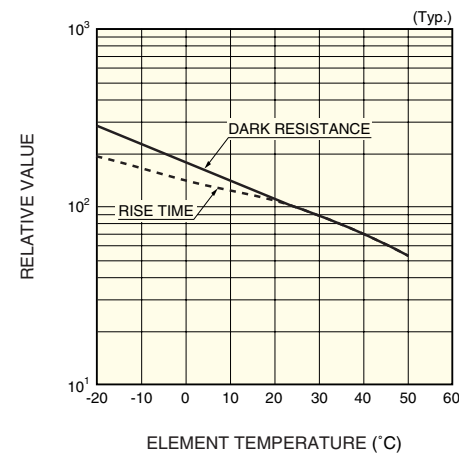
Photo sensitivity temperature characteristic



KIRDB0054EB

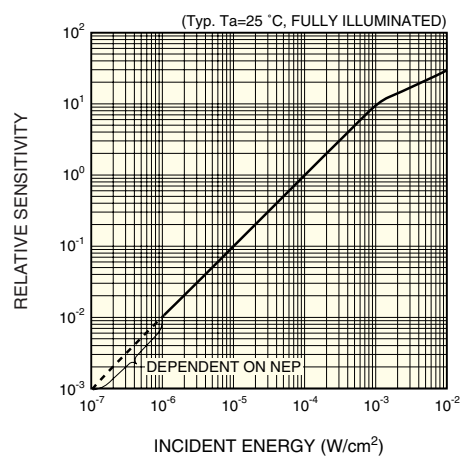
Cooling the device enhances its sensitivity, but the sensitivity also depends on the load resistance in the circuit.

Dark resistance, rise time temperature characteristics



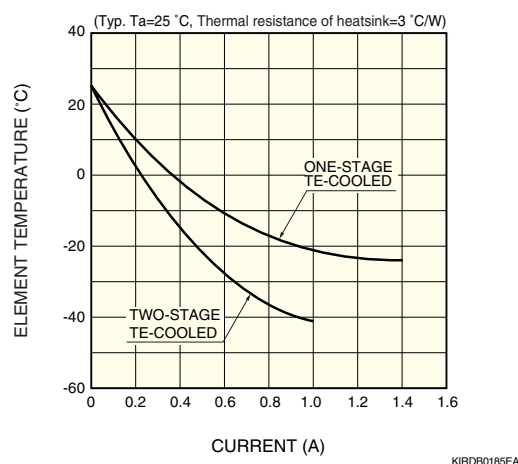
KIRDB0055EB

Photo sensitivity linearity

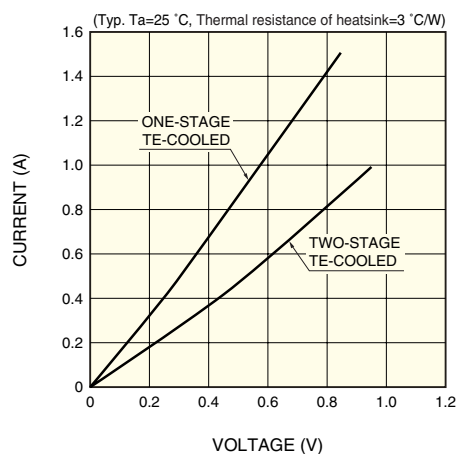


By making the incident light spot smaller than the active area, the upper limit of the linearity becomes lower.

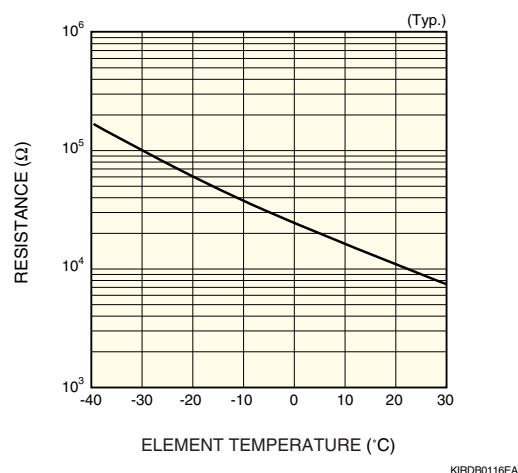
Cooling characteristics of TE-cooler



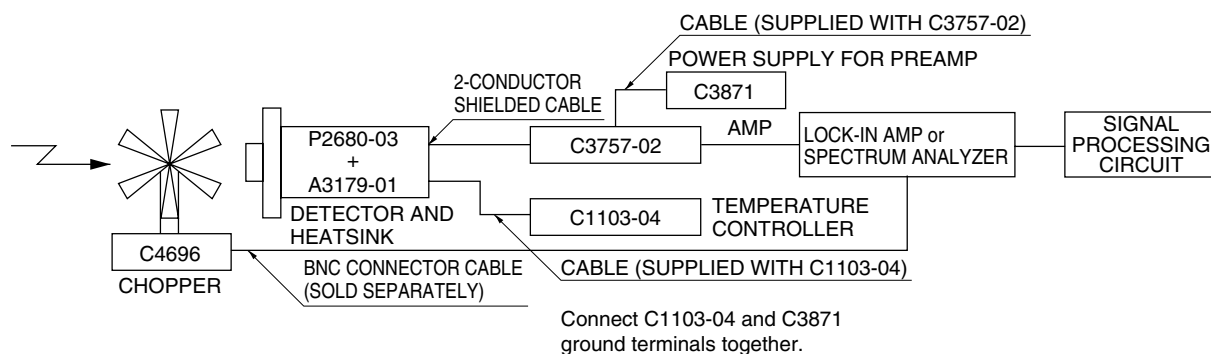
Current vs. voltage characteristics of the TE-cooler



Thermistor temperature characteristic

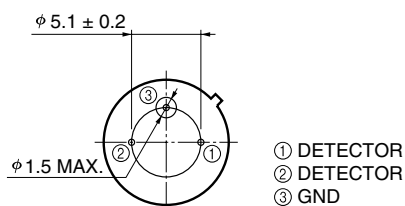
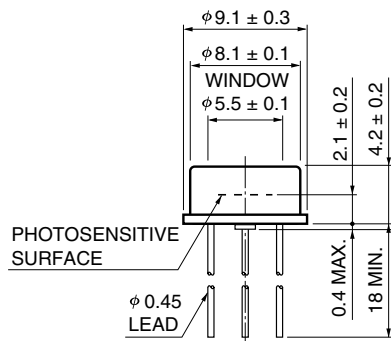


Connection example (P2680-03)



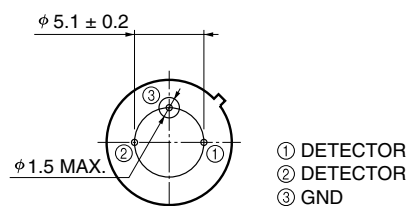
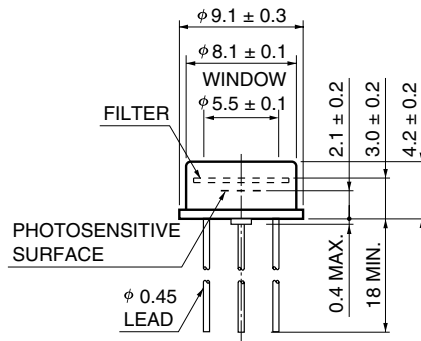
■ Dimensional outlines (unit: mm)

① P791-11/-13



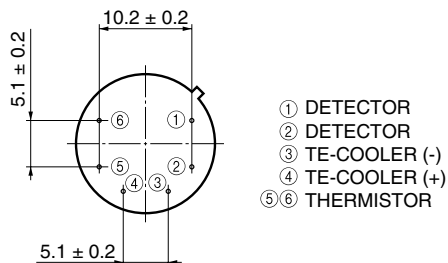
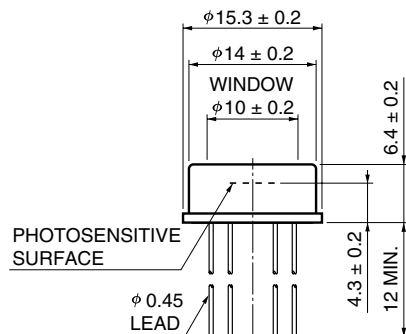
KIRDA0056EC

② P3207-05



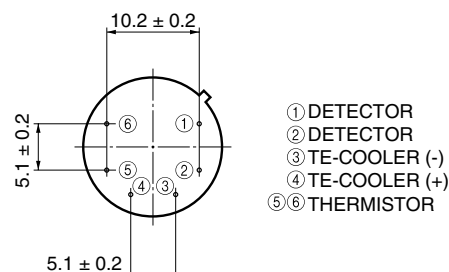
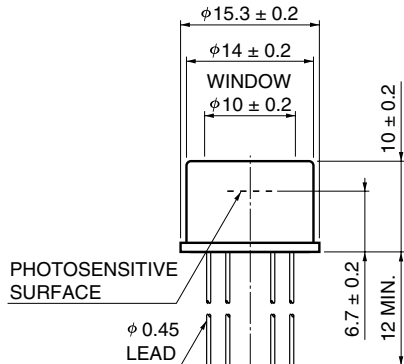
KIRDA0118EA

③ P2038-02/-03



KIRDA0128EA

④ P2680-02/-03



KIRDA0125EA

HAMAMATSU

HAMAMATSU PHOTONICS K.K., Solid State Division

1126-1 Ichino-cho, Hamamatsu City, 435-8558 Japan, Telephone: (81) 053-434-3311, Fax: (81) 053-434-5184, <http://www.hamamatsu.com>

U.S.A.: Hamamatsu Corporation, 360 Foothill Road, P.O.Box 6910, Bridgewater, N.J. 08807-0910, U.S.A., Telephone: (1) 908-231-0960, Fax: (1) 908-231-1218

Germany: Hamamatsu Photonics Deutschland GmbH, Arzbergerstr. 10, D-82211 Herrsching am Ammersee, Germany, Telephone: (49) 08152-3750, Fax: (49) 08152-2658

France: Hamamatsu Photonics France S.A.R.L.: 8, Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: 33-(1) 69 53 71 00, Fax: 33-(1) 69 53 71 10

United Kingdom: Hamamatsu Photonics UK Limited: 2 Howard Court, 10 Tewin Road, Welwyn Garden City, Hertfordshire AL7 1BW, United Kingdom, Telephone: (44) 1707-294888, Fax: (44) 1707-325777

North Europe: Hamamatsu Photonics Norden AB: Smidesvägen 12, SE-171 41 Solna, Sweden, Telephone: (46) 8-509-031-00, Fax: (46) 8-509-031-01

Italy: Hamamatsu Photonics Italia S.R.L.: Strada della Moia, 1/E, 20020 Arese, (Milano), Italy, Telephone: (39) 02-935-81-733, Fax: (39) 02-935-81-741

Information furnished by HAMAMATSU is believed to be reliable. However, no responsibility is assumed for possible inaccuracies or omissions. Specifications are subject to change without notice. No patent rights are granted to any of the circuits described herein. ©2002 Hamamatsu Photonics K.K.